TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74HC4066AP,TC74HC4066AF,TC74HC4066AFN,TC74HC4066AFT

Quad Bilateral Switch

The TC74HC4066A is a high speed CMOS QUAD BILATERAL SWITCH fabricated with silicon gate C²MOS technology.

It consists of four independent high speed switches capable of controlling either digital or analog signals while maintaining the CMOS low power dissipation.

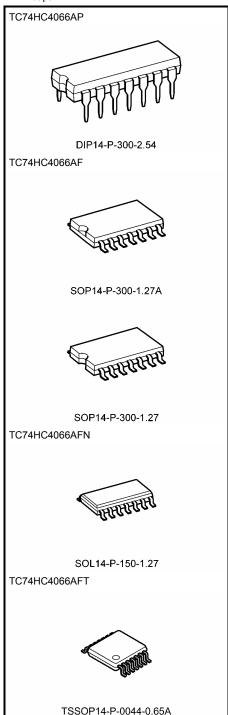
Control input (C) is provided to control the switch. The switch turns ON while the C input is high, and the switch turns OFF while low.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

Features

- High speed: $t_{pd} = 7 \text{ ns (typ.)}$ at $V_{CC} = 5 \text{ V}$
- Low power dissipation: ICC = 1 μ A (max) at Ta = 25°C
- High noise immunity: V_{NIH} = V_{NIL} = 28% V_{CC} (min)
- Low on resistance: $RON = 50 \Omega$ (typ.) at VCC = 9 V
- High degree of linearity: THD = 0.05% (typ.) at $V_{CC} = 5 \text{ V}$
- Pin and function compatible with 4066B

Note: xxxFN (JEDEC SOP) is not available in Japan.

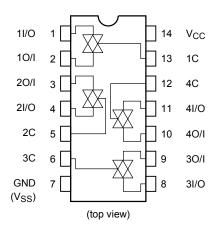


Weight

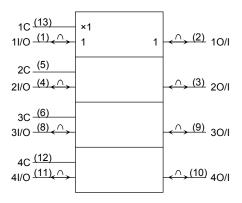
DIP14-P-300-2.54 : 0.96 g (typ.) SOP14-P-300-1.27A : 0.18 g (typ.) SOP14-P-300-1.27 : 0.18 g (typ.) SOL14-P-150-1.27 : 0.12 g (typ.) TSSOP14-P-0044-0.65A : 0.06 g (typ.)



Pin Assignment



IEC Logic Symbol



Truth Table

Control	Switch Function
Н	On
L	Off



Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	-0.5 to 13	V
Control input voltage	V _{IN}	-0.5 to V _{CC} + 0.5	V
Switch I/O voltage	V _{I/O}	-0.5 to V _{CC} + 0.5	V
Control input diode current	I _{IK}	±20	mA
I/O diode current	lok	±20	mA
Switch through Current	l _{OUT}	±25	mA
DC V _{CC} /ground current	I _{CC}	±50	mA
Power dissipation	P _D	500 (DIP) (Note 2)/180 (SOP/TSSOP)	mW
Storage temperature	T _{stg}	−65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Note 2: 500 mW in the range of Ta = -40 to 65°C. From Ta = 65 to 85°C a derating factor of -10 mW/°C should be applied up to 300 mW.

Recommended Operating Conditions (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	2 to 12	V
Control input voltage	V _{IN}	0 to V _{CC}	V
Switch I/O voltage	V _{I/O}	0 to V _{CC}	V
Operating temperature	T _{opr}	-40 to 85	°C
Input rise and fall time	t _{r,} t _f	0 to 1000 (V _{CC} = 2.0 V)	
		0 to 500 (V _{CC} = 4.5 V)	ne
		0 to 400 (V _{CC} = 6.0 V)	ns
		0 to 250 (V _{CC} = 10.0 V)	

Note: The recommended operating conditions are required to ensure the normal operation of the device.
Unused inputs must be tied to either VCC or GND.



Electrical Characteristics

DC Characteristics

Characteristics	Symbol	Test Condition			Га = 25°С		Ta = −40 to 85°C		Unit	
Gridi deteriotico Gymbol		rest odnation	V _{CC} (V)	Min	Тур.	Max	Min	Max	Onit	
			2.0	1.50	_	_	1.50	_		
High-level control	V _{IHC}		4.5	3.15	_	_	3.15	_	٧	
input voltage	VIHC	_	9.0	6.30	_	_	6.30	_		
			12.0	8.40	_	_	8.40	_		
			2.0	_	_	0.50	_	0.50		
Low-level control	V., a		4.5	_	_	1.35	_	1.35	V	
input voltage	V_{ILC}	_	9.0	_	_	2.70	_	2.70	V	
			12.0	_	_	3.60	_	3.60		
		V _{IN} = V _{IHC}	4.5	_	96	170	_	200		
		$V_{I/O} = V_{CC}$ to GND	9.0	_	55	85	_	100		
		I _{I/O} ≤ 1 mA	12.0	_	45	80	_	90		
On resistance	R_{ON}	$V_{IN} = V_{IHC}$ $V_{I/O} = V_{CC}$ or GND $I_{I/O} \le 1$ mA	2.0	_	160	_	_	_	Ω	
			4.5	_	70	100	_	130		
			9.0	_	50	75	_	95		
		/O ≥ 1 A	12.0	_	45	70	_	90		
Difference of on		V _{IN} = V _{IHC}	4.5	_	10	_	_	_		
resistance between	ΔR_{ON}	$V_{I/O} = V_{CC}$ to GND	9.0	_	5	_	_	_	Ω	
switches		I _{I/O} ≤ 1 mA	12.0	_	5	_	_	_		
Input/output leakage		V _{OS} = V _{CC} or GND								
current		V _{IS} = GND or V _{CC}	12.0	_	_	±100	_	±1000	nA	
(switch off)		V _{IN} = V _{ILC}								
Switch input leakage current		VV								
l _{IZ}	I_{IZ}	V _{OS} =V _{CC} or GND V _{IN} = V _{IHC}	12.0	_	- -	±100	_	±1000	nA	
(switch on, output open)		VIN - VIHC								
Control input current	I _{IN}	V _{IN} = V _{CC} or GND	12.0	_	_	±100	_	±1000	nA	
Quiescent supply current	Icc		6.0	_	_	1.0	_	10.0		
		V _{IN} = V _{CC} or GND	9.0	_	_	4.0	_	40.0	μΑ	
			12.0	_	_	8.0	_	80.0		



AC Characteristics ($C_L = 50 \text{ pF}$, input: $t_r = t_f = 6 \text{ ns}$)

Characteristics	Symbol Test Condition			Ta = 25°C		Ta = -40 to 85°C		Unit	
		VCC (V)	Min	Тур.	Max	Min	Max		
			2.0	_	10	50	_	65	
Phase difference between input and	(D) O		4.5	_	4	10	_	13	pF
output	ФІ-О	_	9.0	_	3	8	_	10	
			12.0	_	3	7	_	9	
			2.0	_	18	100	_	125	
Output enable time	t _{pZL}	$R_1 = 1 k\Omega$	4.5	_	8	20	_	25	nE
Output enable time	t _{pZH}	N 1 K22	9.0	_	6	12	_	22	pF
			12.0	_	6	12	_	18	
	t _{pLZ} R	R _L = 1 kΩ	2.0	_	20	115	_	145	pF
Output disable time			4.5	_	10	23	_	29	
Output disable time			9.0	_	8	20	_	25	
			12.0		8	18	-	22	
		$R_L = 1 \text{ k}\Omega$ $C_L = 15 \text{ pF}$	2.0	_	30	_	_	_	MHz
Maximum control			4.5	_	30	_	_	_	
input frequency		V _{OUT} = 1/2 V _{CC}	9.0	_	30	_	_	_	
		AOOL - 1/5 ACC	12.0	_	30	_	_	_	
Control input capacitance	C _{IN}	_			5	10	-	10	pF
Switch terminal capacitance	C _{I/O}	_		_	6	_	_	_	pF
Feed through capacitance	C _{IOS}	_			0.5		_		pF
Power dissipation capacitance	C _{PD}		(Note)		15			_	pF

Note: CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/4 (per channel)$



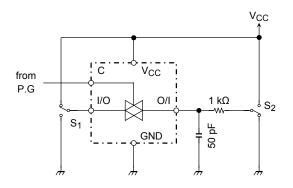
Analog Switch Characteristics (GND = 0 V, Ta = 25°C) (Note)

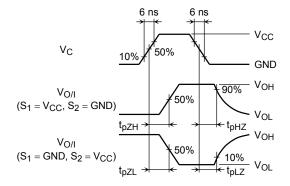
Characteristics	Symbol	Test Condition	V _{CC} (V)	Тур.	Unit
Sine wave distortion (T.H.D)		$f_{\text{IN}} = 1 \text{ kHz}, V_{\text{IN}} = 4 \text{ V}_{\text{p-p}}, @V_{\text{CC}} = 4.5 \text{ V}$ $R_{\text{L}} = 10 \text{ k}\Omega, V_{\text{IN}} = 8 \text{ V}_{\text{p-p}}, @V_{\text{CC}} = 9.0 \text{ V}$ $C_{\text{L}} = 50 \text{ pF}$	4.5 9.0	0.05 0.04	%
Frequency response (switch on)	f _{max}	Adjust f_{IN} voltage to obtain 0dBm at V_{OS} Increase f_{IN} frequency until dB meter reads -3dB R_L = 50 Ω , C_L = 10 pF f_{IN} = 1 MHz, sine wave	4.5 9.0	200 200	MHz
Feedthrough attenuation (switch off)		Vin is centered at $V_{CC}/2$ Adjust input for 0dBm $R_L = 600 \ \Omega, \ C_L = 50 \ pF$ $f_{IN} = 1 \ MHz$, sine wave	4.5 9.0	-60 -60	dB
Crosstalk (control input to signal output)		R_L = 600 Ω, C_L = 50 pF f_{IN} = 1 MHz, square wave (t_r = t_f = 6 ns)	4.5 9.0	60 100	mV
Crosstalk (between any switches)		Adjust V_{IN} to obtain 0dBm at input $R_L = 600 \ \Omega, \ C_L = 50 \ pF$ $f_{IN} = 1 \ MHz$, sine wave	4.5 9.0	-60 -60	dB

Note: These characteristics are determined by design of devices.

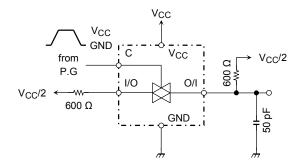
Switching Characteristics Test Circuits

$1. \quad t_{pLZ},\, t_{pHZ},\, t_{pZL},\, t_{pZH}$

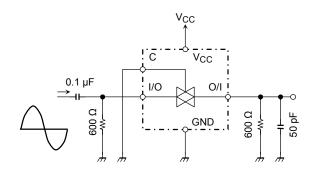




2. Cross Talk (control input-switch output) fIN = 1 MHz duty = 50% tr = tf = 6 ns



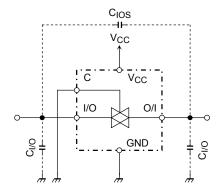
3. Feedthrough Attenuation



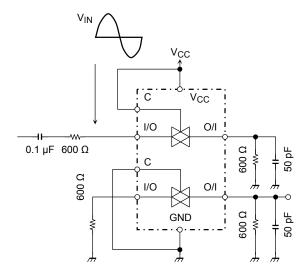
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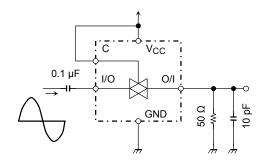
4. C_{IOS}, C_{I/O}



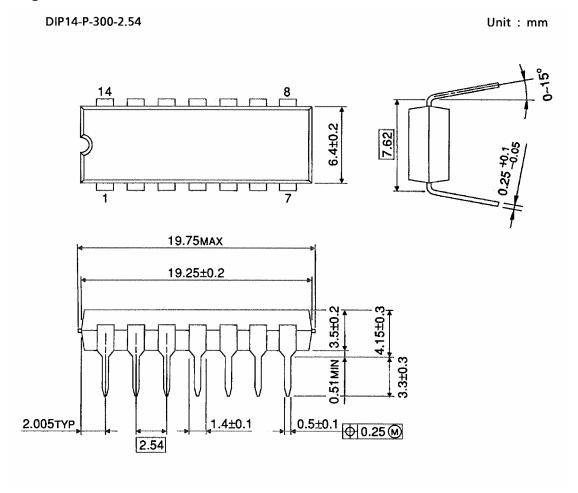
5. Crosstalk (between any two switches)



6. Frequency Response (switch on)

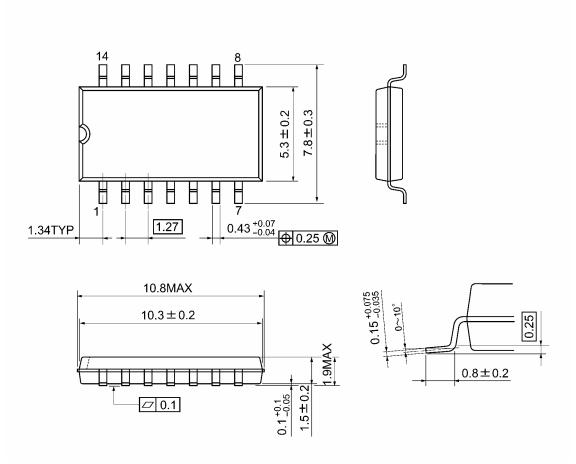






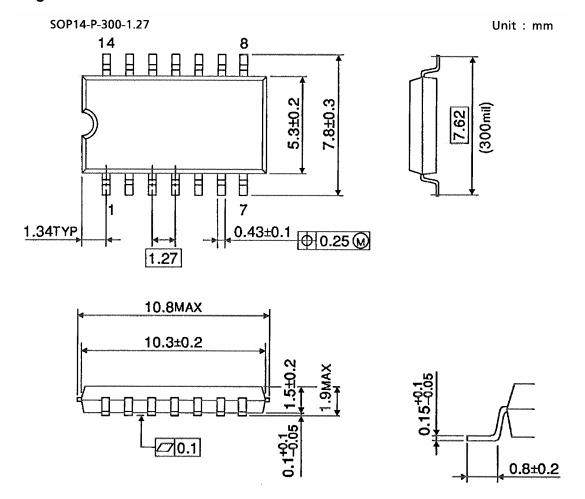
Weight: 0.96 g (typ.)

SOP14-P-300-1.27A Unit: mm



Weight: 0.18 g (typ.)



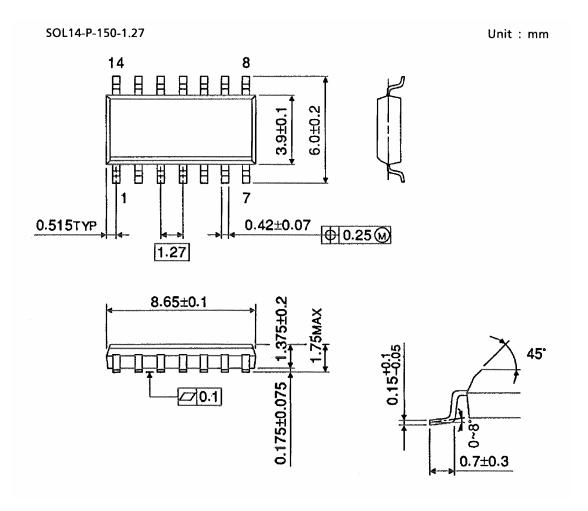


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Weight: 0.18 g (typ.)



Package Dimensions (Note)



Note: This package is not available in Japan.

Weight: 0.12 g (typ.)



TSSOP14-P-0044-0.65A Unit: mm 6.4±0.2 $0.22^{+0.09}_{-0.06}$ 0.65 0.55TYP **⊕**0.13**M** 5.4MAX 5.0±0.1 0~10 1.0±0.05 0.1±0.05 S Ø.1S (0.5)0.45~0.75

Weight: 0.06 g (typ.)

Note: Lead (Pb)-Free Packages

DIP14-P-300-2.54 SOP14-P-300-1.27A SOL14-P-150-1.27 TSSOP14-P-0044-0.65A

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